

# ISO K Line Serial Link Interface

The 33290 is a serial link bus interface device designed to provide bi-directional half-duplex communication interfacing in automotive diagnostic applications. It is designed to interface between the vehicle's on-board microcontroller and systems off-board the vehicle via the special ISO K line. The 33290 is designed to meet the Diagnostic Systems ISO9141 specification. The device's K line bus driver's output is fully protected against bus shorts and overtemperature conditions.

The 33290 derives its robustness to temperature and voltage extremes by being built on a SMARTMOS process, incorporating CMOS logic, bipolar/MOS analog circuitry, and DMOS power FETs. Although the 33290 was principally designed for automotive applications, it is suited for other serial communication applications. It is parametrically specified over an ambient temperature range of  $-40^{\circ}\text{C} \leq T_A \leq 125^{\circ}\text{C}$  and  $8.0\text{ V} \leq V_{BB} \leq 18\text{ V}$  supply. The economical SO-8 surface-mount plastic package makes the 33290 very cost effective.

## Features

- Operates Over Wide Supply Voltage of 8.0 to 18V
- Operating Temperature of  $-40$  to  $125^{\circ}\text{C}$
- Interfaces Directly to Standard CMOS Microprocessors
- ISO K Line Pin Protected Against Shorts to Ground
- Thermal Shutdown with Hysteresis
- ISO K Line Pin Capable of High Currents
- ISO K Line Can Be Driven with up to 10 nF of Parasitic Capacitance
- 8.0 kV ESD Protection Attainable with Few Additional Components
- Standby Mode: No  $V_{\text{Bat}}$  Current Drain with  $V_{\text{DD}}$  at 5.0 V
- Low Current Drain During Operation with  $V_{\text{DD}}$  at 5.0 V
- Pb-Free Packaging Designated by Suffix Code EF

**33290**

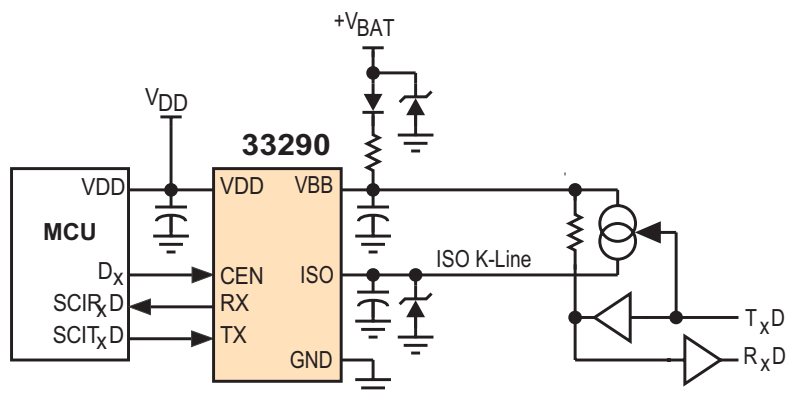
**ISO9141 PHYSICAL INTERFACE**



**D SUFFIX**  
**EF SUFFIX (PB-FREE)**  
**98ASB42564B**  
**8-PIN SOICN**

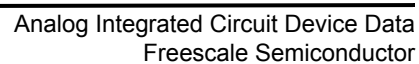
## ORDERING INFORMATION

| Device        | Temperature Range ( $T_A$ )    | Package |
|---------------|--------------------------------|---------|
| MC33290D/R2   | $-40$ to $125^{\circ}\text{C}$ | 8-SOICN |
| MCZ33290EF/R2 |                                |         |

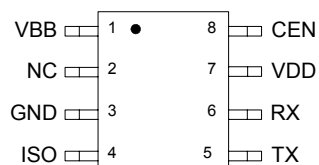


**Figure 1. 33290 Simplified Application Diagram**

## 2



## PIN CONNECTIONS



**Figure 3. 33290 Pin Connections**

**Table 1. 33290 Pin Definitions**

| Pin Number | Pin Name | Definition                                                          |
|------------|----------|---------------------------------------------------------------------|
| 1          | VBB      | Battery power through external resistor and diode.                  |
| 2          | NC       | Not to be connected. <sup>(1)</sup>                                 |
| 3          | GND      | Common signal and power return.                                     |
| 4          | ISO      | Bus connection.                                                     |
| 5          | TX       | Logic level input for data to be transmitted on the bus.            |
| 6          | RX       | Logic output of data received on the bus.                           |
| 7          | VDD      | Logic power source input.                                           |
| 8          | CEN      | Chip enable. Logic "1" for active state. Logic "0" for sleep state. |

**Notes**

1. NC pins should not have any connections made to them. NC pins are not guaranteed to be open circuits.

## ELECTRICAL CHARACTERISTICS

## MAXIMUM RATINGS

Table 2. Maximum Ratings

All voltages are with respect to ground unless otherwise noted. Exceeding these ratings may cause a malfunction or permanent damage to the device.

| Rating                                                                                        | Symbol                   | Value                   | Unit |
|-----------------------------------------------------------------------------------------------|--------------------------|-------------------------|------|
| VDD DC Supply Voltage                                                                         | $V_{DD}$                 | -0.3 to 7.0             | V    |
| VBB Load Dump Peak Voltage                                                                    | $V_{BB(LD)}$             | 45                      | V    |
| ISO Pin Load Dump Peak Voltage <sup>(2)</sup>                                                 | $V_{ISO}$                | 40                      | V    |
| ISO Short Circuit Current Limit                                                               | $I_{ISO(LIM)}$           | 1.0                     | A    |
| ESD Voltage <sup>(3)</sup><br>Human Body Model <sup>(4)</sup><br>Machine Model <sup>(4)</sup> | $V_{ESD1}$<br>$V_{ESD2}$ | $\pm 2000$<br>$\pm 200$ | V    |
| ISO Clamp Energy <sup>(5)</sup>                                                               | $E_{clamp}$              | 10                      | mJ   |
| Storage Temperature                                                                           | $T_{stg}$                | -55 to +150             | °C   |
| Operating Case Temperature                                                                    | $T_C$                    | -40 to +125             | °C   |
| Operating Junction Temperature                                                                | $T_J$                    | -40 to +150             | °C   |
| Power Dissipation<br>$T_A = 25^\circ\text{C}$                                                 | $P_D$                    | 0.8                     | W    |
| Peak Package Reflow Temperature During Reflow <sup>(6), (7)</sup>                             | $T_{PPRT}$               | Note 7.                 | °C   |
| Thermal Resistance<br>Junction-to-Ambient                                                     | $R_{\theta JA}$          | 150                     | °C/W |

## Notes

- Device will survive double battery jump start conditions in typical applications for 10 minutes duration, but is not guaranteed to remain within specified parametric limits during this duration.
- ESD data available upon request.
- ESD1 testing is performed in accordance with the Human Body Model ( $C_{ZAP} = 100 \text{ pF}$ ,  $R_{ZAP} = 1500 \Omega$ ), ESD2 testing is performed in accordance with the Machine Model ( $C_{ZAP} = 200 \text{ pF}$ ,  $R_{ZAP} = 0 \Omega$ ).
- Nonrepetitive clamping capability at 25°C.
- Pin soldering temperature limit is for 10 seconds maximum duration. Not designed for immersion soldering. Exceeding these limits may cause malfunction or permanent damage to the device.
- Freescall's Package Reflow capability meets Pb-free requirements for JEDEC standard J-STD-020C. For Peak Package Reflow Temperature and Moisture Sensitivity Levels (MSL), Go to [www.freescale.com](http://www.freescale.com), search by part number [e.g. remove prefixes/suffixes and enter the core ID to view all orderable parts. (i.e. MC33xxxD enter 33xxx), and review parametrics.

## STATIC ELECTRICAL CHARACTERISTICS

**Table 3. Static Electrical Characteristics**

Characteristics noted under conditions of  $4.75\text{ V} \leq V_{DD} \leq 5.25\text{ V}$ ,  $8.0\text{ V} \leq V_{BB} \leq 18\text{ V}$ ,  $-40^\circ\text{C} \leq T_C \leq 125^\circ\text{C}$ , unless otherwise noted.

| Characteristic                                                                                                         | Symbol                         | Min                 | Typ    | Max                 | Unit             |
|------------------------------------------------------------------------------------------------------------------------|--------------------------------|---------------------|--------|---------------------|------------------|
| <b>POWER AND CONTROL</b>                                                                                               |                                |                     |        |                     |                  |
| $V_{DD}$ Sleep State Current<br>$T_X = 0.8 V_{DD}$ , $CEN = 0.3 V_{DD}$                                                | $I_{DD(SS)}$                   | —                   | —      | 0.1                 | mA               |
| $V_{DD}$ Quiescent Operating Current<br>$T_X = 0.2 V_{DD}$ , $CEN = 0.7 V_{DD}$                                        | $I_{DD(Q)}$                    | —                   | —      | 1.0                 | mA               |
| $V_{BB}$ Sleep State Current<br>$V_{BB} = 16\text{ V}$ , $T_X = 0.8 V_{DD}$ , $CEN = 0.3 V_{DD}$                       | $I_{BB(SS)}$                   | —                   | —      | 50                  | $\mu\text{A}$    |
| $V_{BB}$ Quiescent Operating Current<br>$T_X = 0.2 V_{DD}$ , $CEN = 0.7 V_{DD}$                                        | $I_{BB(Q)}$                    | —                   | —      | 1.0                 | mA               |
| Chip Enable<br>Input High-Voltage Threshold <sup>(8)</sup><br>Input Low-Voltage Threshold <sup>(9)</sup>               | $V_{IH(CEN)}$<br>$V_{IL(CEN)}$ | $0.7 V_{DD}$<br>—   | —<br>— | —<br>$0.3 V_{DD}$   | V                |
| Chip Enable Pull-Down Current <sup>(10)</sup>                                                                          | $I_{PD(CEN)}$                  | 2.0                 | —      | 40                  | $\mu\text{A}$    |
| $T_X$ Input Low-Voltage Threshold<br>$R_{ISO} = 510\ \Omega$ <sup>(11)</sup>                                           | $V_{IL(Tx)}$                   | —                   | —      | $0.3 \times V_{DD}$ | V                |
| $T_X$ Input High-Voltage Threshold<br>$R_{ISO} = 510\ \Omega$ <sup>(12)</sup>                                          | $V_{IH(Tx)}$                   | $0.7 \times V_{DD}$ | —      | —                   | V                |
| $T_X$ Pull-Up Current <sup>(13)</sup>                                                                                  | $I_{PU(Tx)}$                   | -40                 | —      | -2.0                | $\mu\text{A}$    |
| $R_X$ Output Low-Voltage Threshold<br>$R_{ISO} = 510\ \Omega$ , $T_X = 0.2 V_{DD}$ , $R_X$ Sinking 1.0 mA              | $V_{OL(Rx)}$                   | —                   | —      | $0.2 V_{DD}$        | V                |
| $R_X$ Output High-Voltage Threshold<br>$R_{ISO} = 510\ \Omega$ , $T_X = 0.8 V_{DD}$ , $R_X$ Sourcing 250 $\mu\text{A}$ | $V_{OH(Rx)}$                   | $0.8 V_{DD}$        | —      | —                   | V                |
| Thermal Shutdown <sup>(14)</sup>                                                                                       | $T_{LIM}$                      | 150                 | 170    | —                   | $^\circ\text{C}$ |

## Notes

8. When IBB transitions to  $>100\ \mu\text{A}$ .
9. When IBB transitions to  $<100\ \mu\text{A}$ .
10. Enable pin has an internal current pull-down. Pull-down current is measured with CEN pin at  $0.3 V_{DD}$ .
11. Measured by ramping  $T_X$  down from  $0.7 V_{DD}$  and noting  $T_X$  value at which ISO falls below  $0.2 V_{BB}$ .
12. Measured by ramping  $T_X$  up from  $0.3 V_{DD}$  and noting the value at which ISO rises above  $0.9 V_{BB}$ .
13.  $T_X$  pin has internal current pull-up. Pull-up current is measured with  $T_X$  pin at  $0.7 V_{DD}$ .
14. Thermal Shutdown performance ( $T_{LIM}$ ) is guaranteed by design but not production tested.

**Table 3. Static Electrical Characteristics (Continued)**

Characteristics noted under conditions of  $4.75\text{ V} \leq V_{DD} \leq 5.25\text{ V}$ ,  $8.0\text{ V} \leq V_{BB} \leq 18\text{ V}$ ,  $-40^{\circ}\text{C} \leq T_C \leq 125^{\circ}\text{C}$ , unless otherwise noted.

| Characteristic                                                                                                                   | Symbol         | Min                  | Typ | Max                 | Unit          |
|----------------------------------------------------------------------------------------------------------------------------------|----------------|----------------------|-----|---------------------|---------------|
| <b>ISO I/O</b>                                                                                                                   |                |                      |     |                     |               |
| Input Low Voltage Threshold<br>$R_{ISO} = 0\ \Omega$ , $T_X = 0.8\ V_{DD}$ <sup>(15)</sup>                                       | $V_{IL(ISO)}$  | –                    | –   | $0.4 \times V_{BB}$ | V             |
| Input High Voltage Threshold<br>$R_{ISO} = 0\ \Omega$ , $T_X = 0.8\ V_{DD}$ <sup>(16)</sup>                                      | $V_{IH(ISO)}$  | $0.7 \times V_{BB}$  | –   | –                   | V             |
| Input Hysteresis <sup>(17)</sup>                                                                                                 | $V_{Hys(ISO)}$ | $0.05 \times V_{BB}$ | –   | $0.1 \times V_{BB}$ | V             |
| Internal Pull-Up Current<br>$R_{ISO} = \infty\ \Omega$ , $T_X = 0.8\ V_{DD}$ , $V_{ISO} = 9.0\text{ V}$ , $V_{BB} = 18\text{ V}$ | $I_{PU(ISO)}$  | -5.0                 | –   | -140                | $\mu\text{A}$ |
| Short Circuit Current Limit <sup>(18)</sup><br>$R_{ISO} = 0\ \Omega$ , $T_X = 0.4\ V_{DD}$ , $V_{ISO} = V_{BB}$                  | $I_{SC(ISO)}$  | 50                   | –   | 1000                | mA            |
| Output Low Voltage<br>$R_{ISO} = 510\ \Omega$ , $T_X = 0.2\ V_{DD}$                                                              | $V_{OL(ISO)}$  | –                    | –   | $0.1 \times V_{BB}$ | V             |
| Output High Voltage<br>$R_{ISO} = \infty\ \Omega$ , $T_X = 0.8\ V_{DD}$                                                          | $V_{OH(ISO)}$  | $0.95 \times V_{BB}$ | –   | –                   | V             |

**Notes**

15. ISO ramped from  $0.8\ V_{BB}$  to  $0.4\ V_{BB}$ , Monitor  $R_X$ , Value of ISO voltage at which  $R_X$  transitions to  $0.3\ V_{DD}$ .
16. ISO ramped from  $0.4\ V_{BB}$  to  $0.8\ V_{BB}$ , Monitor  $R_X$ , Value of ISO voltage at which  $R_X$  transitions to  $0.7\ V_{DD}$ .
17. Input Hysteresis,  $V_{Hys(ISO)} = V_{IH(ISO)} - V_{IL(ISO)}$ .
18. ISO has internal current limiting.

**DYNAMIC ELECTRICAL CHARACTERISTICS****Table 4. Dynamic Electrical Characteristics**

Characteristics noted under conditions of  $4.75\text{ V} \leq V_{DD} \leq 5.25\text{ V}$ ,  $8.0\text{ V} \leq V_{BB} \leq 18\text{ V}$ ,  $-40^{\circ}\text{C} \leq T_C \leq 125^{\circ}\text{C}$ , unless otherwise noted.

| Characteristic                                                                                                                                                                                                | Symbol          | Min    | Typ    | Max        | Unit          |
|---------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----------------|--------|--------|------------|---------------|
| Fall Time <sup>(19)</sup><br>$R_{ISO} = 510\ \Omega$ to $V_{BB}$ , $C_{ISO} = 10\text{ nF}$ to Ground                                                                                                         | $t_{fall(ISO)}$ | –      | –      | 2.0        | $\mu\text{s}$ |
| ISO Propagation Delay <sup>(20)</sup><br>High to Low: $R_{ISO} = 510\ \Omega$ , $C_{ISO} = 500\text{ pF}$ <sup>(21)</sup><br>Low to High: $R_{ISO} = 510\ \Omega$ , $C_{ISO} = 500\text{ pF}$ <sup>(22)</sup> | $t_{PD(ISO)}$   | –<br>– | –<br>– | 2.0<br>2.0 | $\mu\text{s}$ |

**Notes**

19. Time required ISO voltage to transition from  $0.8\ V_{BB}$  to  $0.2\ V_{BB}$ .
20. Changes in the value of  $C_{ISO}$  affect the rise and fall time but have minimal effect on Propagation Delay.
21. Step  $T_X$  voltage from  $0.2\ V_{DD}$  to  $0.8\ V_{DD}$ . Time measured from  $V_{IH(ISO)}$  until  $V_{ISO}$  reaches  $0.3\ V_{BB}$ .
22. Step  $T_X$  voltage from  $0.8\ V_{DD}$  to  $0.2\ V_{DD}$ . Time measured from  $V_{IL(ISO)}$  until  $V_{ISO}$  reaches  $0.7\ V_{BB}$ .

## ELECTRICAL PERFORMANCE CURVES

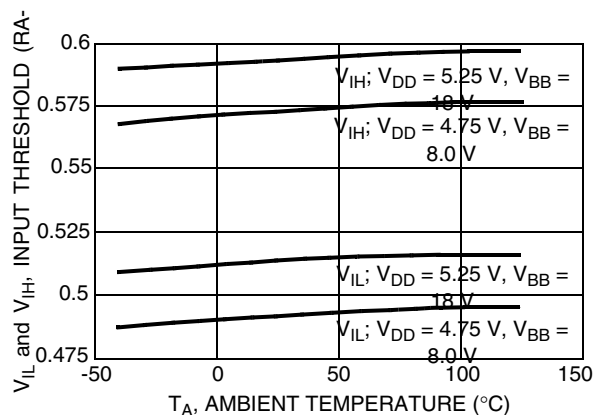


Figure 4. ISO Input Threshold/ $V_{BB}$  vs. Temperature

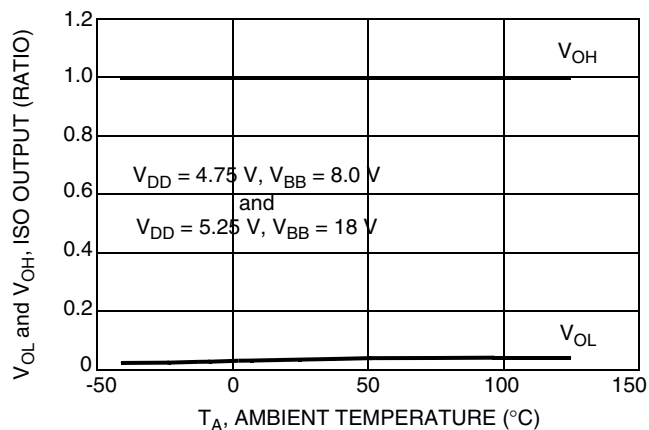


Figure 6. ISO Fall Time vs. Temperature

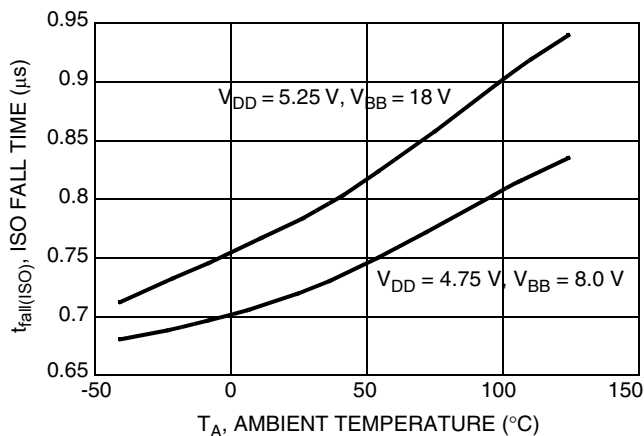


Figure 5. ISO Output/ $V_{BB}$  vs. Temperature

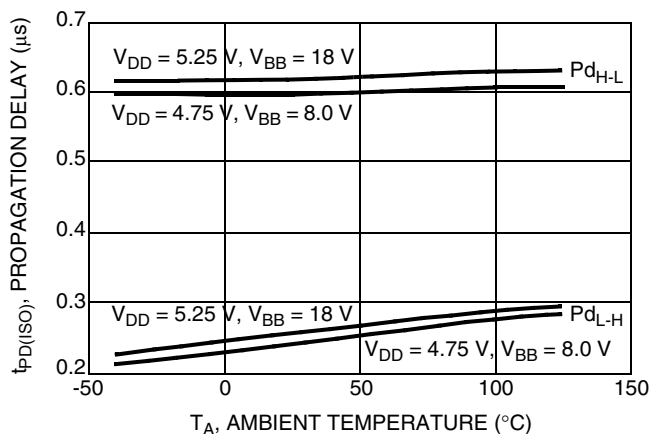


Figure 7. ISO Propagation Delay vs. Temperature

## TYPICAL APPLICATIONS

### INTRODUCTION

The 33290 is a serial link bus interface device conforming to the ISO 9141 physical bus specification. The device was designed for automotive environment usage compliant with On-Board Diagnostic (OBD) requirements set forth by the California Air Resources Board (CARB) using the ISO K line. The device does not incorporate an ISO L line. It provides bi-directional half-duplex communications interfacing from a

microcontroller to the communication bus. The 33290 incorporates circuitry to interface the digital translations from 5.0 V microcontroller logic levels to battery level logic and from battery level logic to 5.0 V logic levels. The 33290 is built using Freescale Semiconductor's SMARTMOS process and is packaged in an 8-pin plastic SOIC.

### FUNCTIONAL DESCRIPTION

The 33290 transforms 5.0 V microcontroller logic signals to battery level logic signals and visa versa. The maximum data rate is set by the fall time and the rise time. The fall time is set by the output driver. The rise time is set by the bus capacitance and the pull-up resistors on the bus. The fall time of the 33290 allows data rates up to 150 kbps using a 30 percent maximum bit time transition value. The serial link interface will remain fully functional over a battery voltage range of 6.0 to 18 V. The device is parametrically specified over a dynamic  $V_{BB}$  voltage range of 8.0 to 18 V.

Required input levels from the microcontroller are ratio-metric with the  $V_{DD}$  voltage normally used to power the microcontroller. This enhances the 33290's ability to remain in harmony with the  $R_X$  and  $T_X$  control input signals of the microcontroller. The  $R_X$  and  $T_X$  control inputs are compatible with standard 5.0 V CMOS circuitry. For fault-tolerant purposes the  $T_X$  input from the microcontroller has an internal

passive pull-up to  $V_{DD}$ , while the CEN input has an internal passive pull-down to ground.

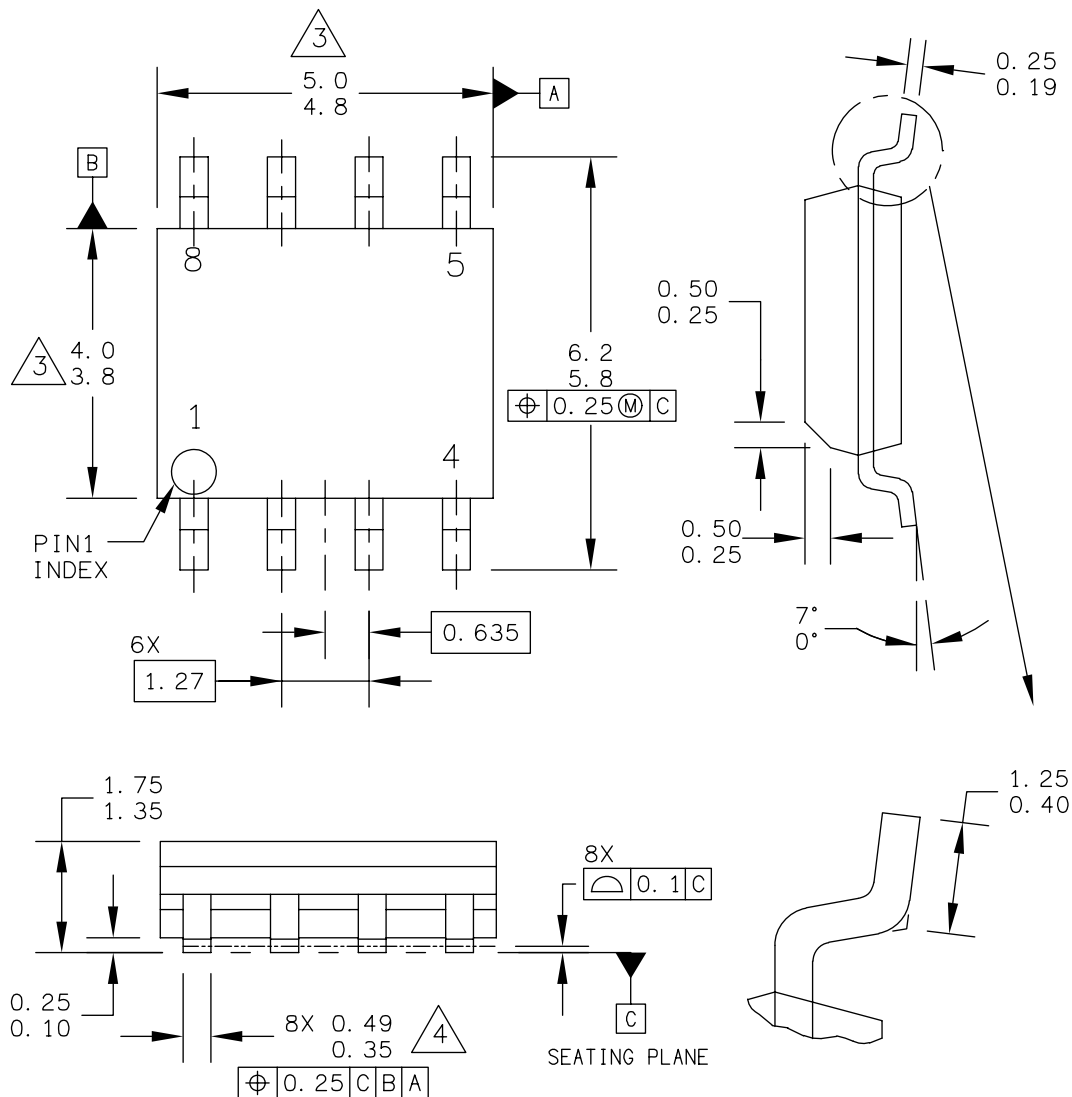
A pull-up to battery is internally provided as well as an active data pull-down. The internal active pull-down is current-limit-protected against shorts to battery and further protected by thermal shutdown. Typical applications have reverse battery protection by the incorporation of an external 510  $\Omega$  pull-up resistor and diode to battery.

Reverse battery protection of the device is provided by using a reverse battery blocking diode ("D" in the Simplified Application Diagram on page 1). Battery line transient protection of the device is provided for by using a 45 V zener and a 500  $\Omega$  resistor connected to the  $V_{BB}$  source as shown in the same diagram. Device ESD protection from the communication lines exiting the module is through the use of the capacitor connected to the  $V_{BB}$  device pin and the capacitor used in conjunction with the 27 V zener connected to the ISO pin.

## PACKAGING

## PACKAGE DIMENSIONS

For the most current package revision, visit [www.freescale.com](http://www.freescale.com) and perform a keyword search using the “98A” listed below.



|                                                         |  |                           |  |                            |  |
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|                                                         |  | CASE NUMBER: 751-07       |  | 07 APR 2005                |  |
|                                                         |  | STANDARD: JEDEC MS-012AA  |  |                            |  |

D SUFFIX  
EF SUFFIX (PB-FREE)  
8-PIN  
PLASTIC PACKAGE  
98ASB42564B  
REV. U

## REVISION HISTORY

| REVISION | DATE    | DESCRIPTION OF CHANGES                                                                                                                                                                                                                                                                                     |
|----------|---------|------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| 6.0      | 7/2006  | <ul style="list-style-type: none"><li>• Implemented Revision History page</li><li>• Converted to Freescale format and updated to the prevailing for and style</li><li>• Added Pb-free suffix EF</li><li>• Removed MC33290EG/R2 and replaced with MCZ33290EG/R2 in the Ordering Information block</li></ul> |
| 7.0      | 10/2006 | <ul style="list-style-type: none"><li>• Removed Peak Package Reflow Temperature During Reflow (solder reflow) parameter from <a href="#">Maximum Ratings on page 4</a>. Added note with instructions to obtain this information from <a href="http://www.freescale.com">www.freescale.com</a>.</li></ul>   |
| 8.0      | 8/2008  | <ul style="list-style-type: none"><li>• Corrected the Document header information.</li><li>• Updated to the current Freescale form and style.</li></ul>                                                                                                                                                    |

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